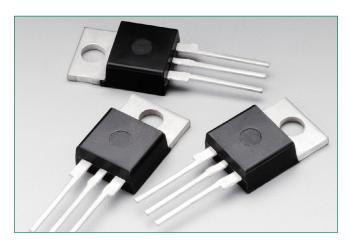
# MAC16CMG, MAC16CNG

TRIAC - 400V - 800V







#### **Additional Information**











Resources

Accessories

Samples

### **Functional Diagram**



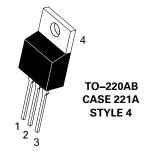
### **Description**

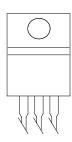
Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever fullwave, silicon gate-controlled devices are needed.

#### **Features**

- High Commutating di/dt and High Immunity to dV/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability - 150 Amperes
- Industry Standard TO-220 Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- These Devices are Pb-Free and are RoHS Compliant

#### **Pin Out**





# **MAC16CMG, MAC16CNG** TRIAC - 400V - 800V

### **Maximum Ratings** (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (- 40 to 125°C)	1		600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 8$	0°C)	I <sub>T (RMS)</sub>	16	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)		I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	93	A²sec
Peak Gate Power ( $T_c = 80^{\circ}$ C, Pulse Width $\leq 1.0 \mu$ s)		P <sub>GM</sub>	20	W
Average Gate Power (t = $8.3 \text{ ms}$ , $T_c = 80^{\circ}\text{C}$ )		P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range		T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 10 seconds	s, 1/8" from case for	T <sub>L</sub>	260	°C

### **Electrical Characteristics - OFF** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	A
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T <sub>J</sub> = 125°C	I	-	-	2.0	mA

### Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) (I <sub>TM</sub> = ±21 A Peak)		$V_{TM}$	-	1.2	1.6	V
Gate Trigger Current	MT2(+), G(+)		8.0	12	35	
(Continuous dc)	MT2(+), G(-)	I <sub>GT</sub>	8.0	16	35	mA
$(V_{D} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	MT2(-), G(-)		8.0	20	35	
Gate Trigger Voltage (Continuous dc)	MT2(+), G(+)		0.5	0.75	1.5	
	MT2(+), G(-)	V <sub>GT</sub>	0.5	0.72	1.5	V
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		_	25	50	
Latching Current $(V_D = 24 \text{ V, } I_S = 35 \text{ mA})$	MT2(+), G(-)	I <sub>L</sub>	_	40	80	V
(v <sub>D</sub> - 2- v, i <sub>G</sub> - 30 iii) y	MT2(-), G(-)		_	24	50	
Holding Current ( $V_D = 12 V_{dc}$ , Gate Open, Initiating Current = ±150 mA)		I <sub>H</sub>	-	20	40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different

<sup>2.</sup> Indicates Pulse Test: Pulse Width  $\leq 2.0$  ms, Duty Cycle  $\leq 2\%$ 



Recommended Operating Conditions may affect device reliability.

1. V<sub>DBM</sub> and V<sub>SBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

# MAC16CMG, MAC16CNG TRIAC – 400V - 800V

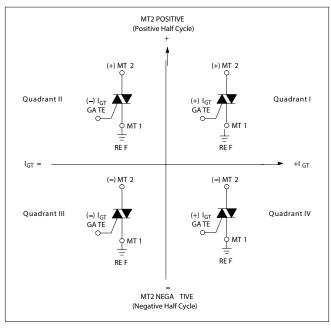
# **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dV/dt = 24 V/ $\mu$ s, Gate Open, $T_J = 125^{\circ}$ C, f = 250 Hz, $C_L = 10 \mu$ F, $L_L = 40 \text{ mH}$ , with Snubber)	(di/dt)c	15	-	-	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM'}$ , Exponential Waveform, Gate Open, $T_J = 125$ °C)	dv/dt	600	_	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz	di/dt	_	_	10	A/µs

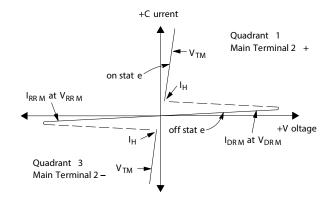
## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1. With in – phase signals (using standard AC lines) quadrants I and III are used



# MAC16CMG, MAC16CNG TRIAC – 400V - 800V

Figure 1. Typical Gate Trigger Current vs Junction Temperature

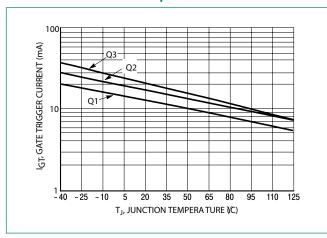
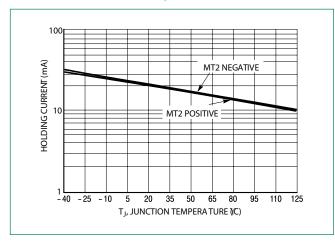


Figure 3. Typical Holding Current vs Junction Temperature



**Figure 5. Typical RMS Current Derating** 

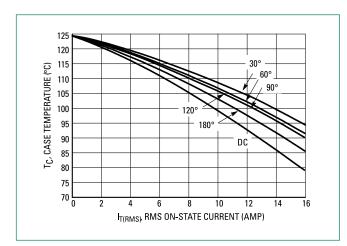


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

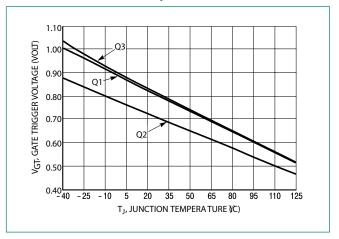


Figure 4. Typical Latching Current vs Junction
Temperature

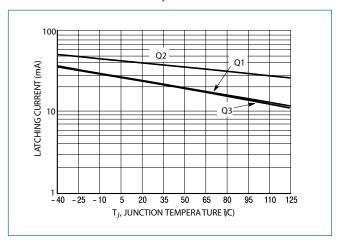
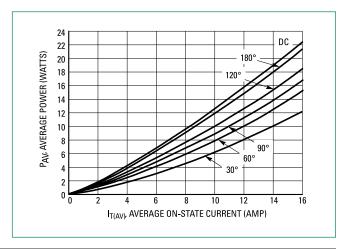


Figure 6. On-State Power Dissipation





# MAC16CMG, MAC16CNG TRIAC – 400V - 800V

**Figure 7. On-State Characteristics** 

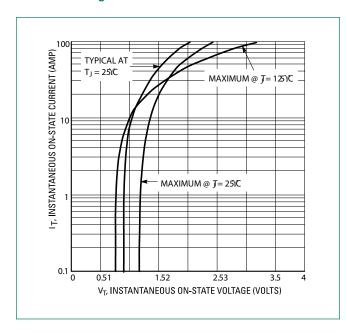
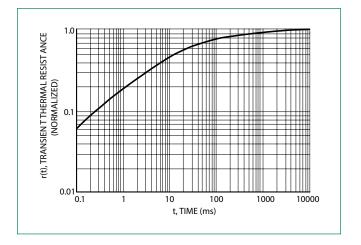


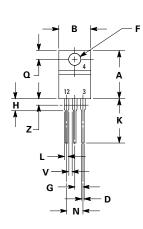
Figure 8. Typical Thermal Response

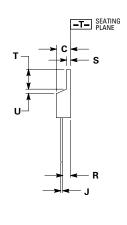




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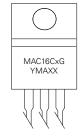
#### **Dimensions**





# **Part Marking System**





Y =Year M =Month A =Assembly Site

XX =Lot Serial Code G =Pb-Free Package

Di	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	Main Terminal 2			

### **Ordering Information**

Device	Package	Shipping
MAC16CMG	TO-220AB	1000 Unito / Day
MAC16CNG	(Pb-Free)	1000 Units / Box

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.



<sup>1.</sup> Dimensioning and tolerancing per ansi y14.5m, 1982.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Littelfuse:

MAC16CNG MAC16CMG